

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
700V	0.8Ω@10V	12A

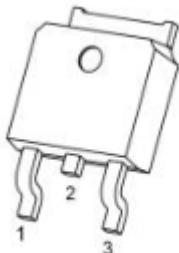
Feature

- Fast Switching
- Improved dv/dt capability
- 100% Single Pulse avalanche energy Test

Applications

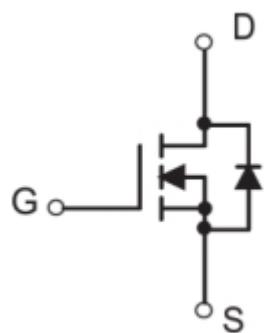
- DC Motor Control and Class D Amplifier
- Uninterruptible Power Supply (UPS)

Package



TO-252-2L(G:1 D:2 S:3)

Circuit diagram



Marking



12N70 : Product code
** : Week code.

Absolute maximum ratings

($T_a = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	700	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_c = 25^\circ\text{C}$)	I_D	12	W
Pulsed Drain Current	I_{DM}	48	A
Single Pulse Avalanche Energy	E_{AS}	550	mJ
Power Dissipation ($T_c = 25^\circ\text{C}$)	P_D	55	W
Thermal Resistance Junction- Case	$R_{\theta JC}$	2.27	$^\circ\text{C} / \text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ\text{C}$

Electrical characteristics

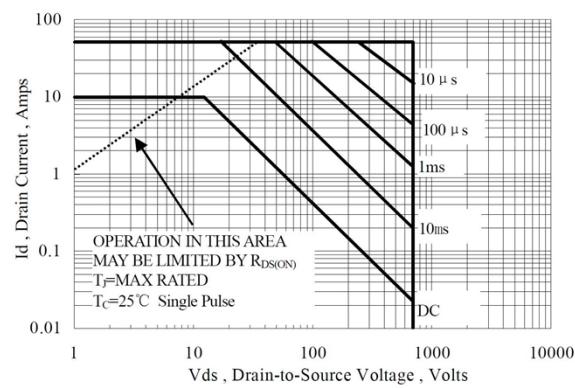
($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	700			V
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = 700\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 25^\circ\text{C}$			10	μA
Gate-body leakage current	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}, V_{\text{DS}} = 0\text{V}$			± 100	μA
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	2		4	V
Static Drain-Source On-Resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}} = 10\text{V}, I_D = 5\text{A}$		0.8	1	Ω
Dynamic characteristics⁴						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 25\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		1852		pF
Output Capacitance	C_{oss}			190		
Reverse Transfer Capacitance	C_{rss}			20		
Total Gate Charge(4.5V)	Q_g	$V_{\text{DS}} = 520\text{V}, V_{\text{GS}} = 10\text{V}, I_D = 18\text{A}$		42		nC
Gate-Source Charge	Q_{gs}			9		
Gate-Drain Charge	Q_{gd}			18.3		
Switching Characteristics						
Turn-On Delay Time	$T_{\text{d(on)}}$	$V_{\text{DS}} = 15\text{V}, I_D = 5.5\text{A}, R_{\text{GEN}} = 1.8\Omega, V_{\text{GS}} = 4.5\text{V}$		30		nS
Rise Time	T_r			115		
Turn-Off Delay Time	$T_{\text{d(off)}}$			95		
Fall Time	T_f			85		
Drain-Source Diode Characteristics and Maximum Ratings						
Maximum Continuous Drain to Source Diode Forward Current	I_s				130	A
Maximum Pulsed Drain to Source Diode Forward Current	I_{SM}				360	A
Drain to Source Diode Forward Voltage	V_{SD}	$V_{\text{GS}} = 0\text{V}, I_s = 20\text{A}$			1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 60\text{A}, dI/dt = 100\text{A}/\mu\text{s}$		56		ns
Body Diode Reverse Recovery Time Charge	Q_{rr}			110		nC

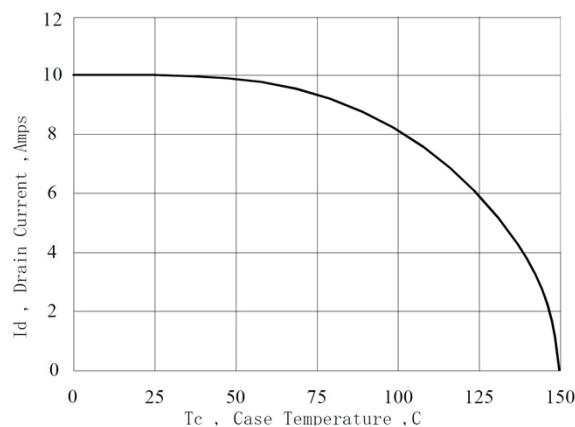
Note :

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: $T_J = 25^\circ\text{C}, V_G = 10\text{V}, L = 30\text{mH}, R_g = 25\Omega, V_{\text{DD}} = 100\text{V}$

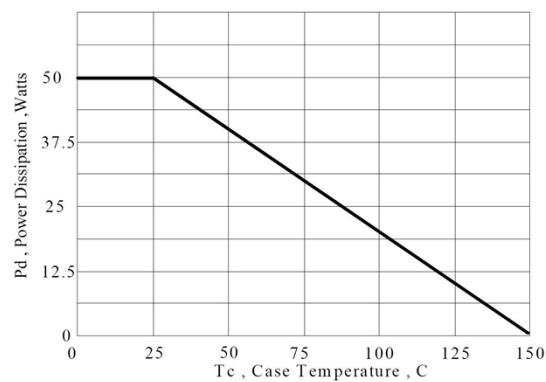
Typical Characteristics



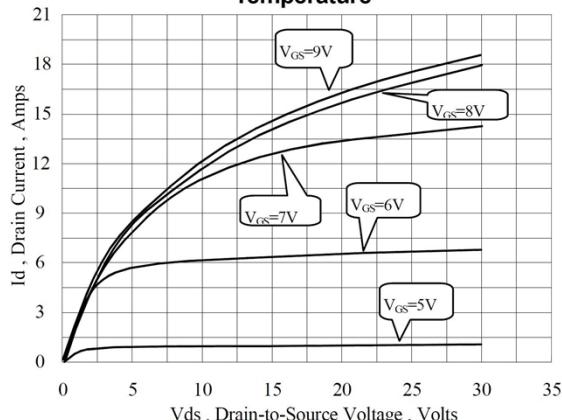
Maximum Forward Bias Safe Operating Area



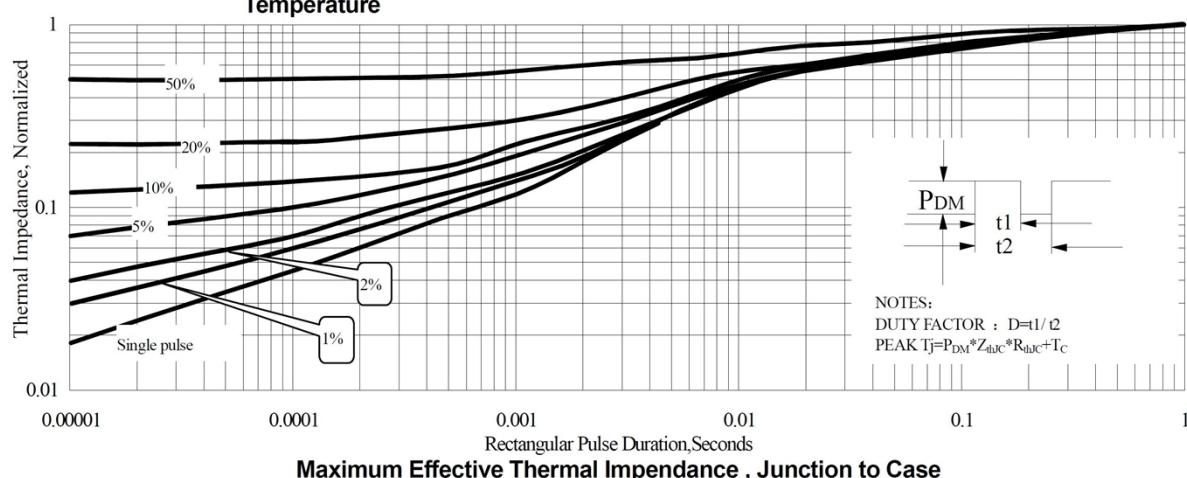
Maximum Continuous Drain Current vs Case Temperature



Maximum Power Dissipation vs Case Temperature



Typical Output Characteristics

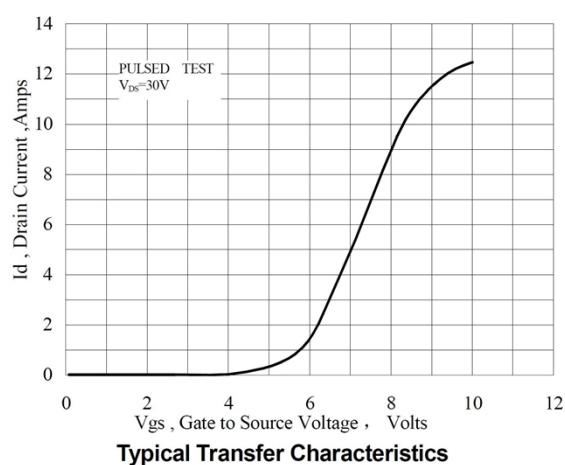
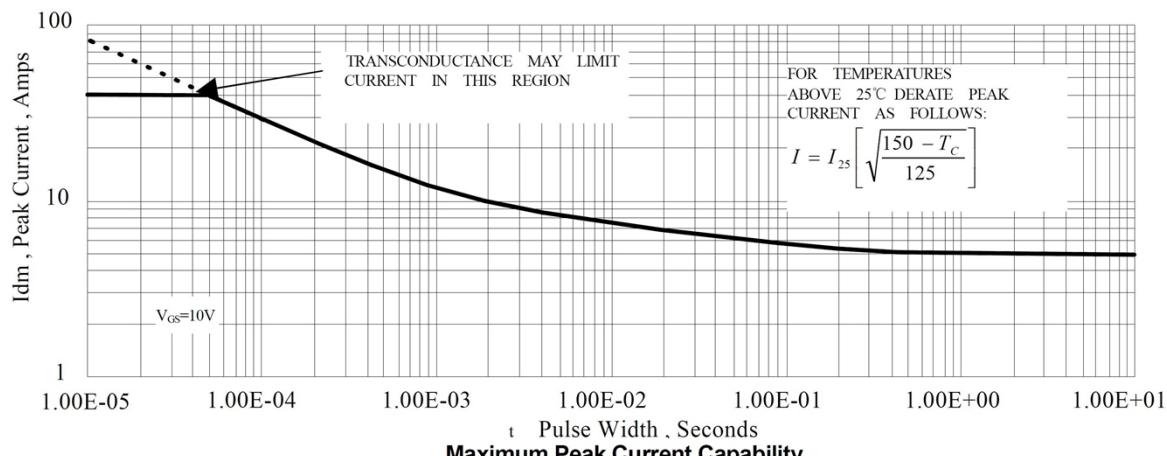


Maximum Effective Thermal Impedance , Junction to Case

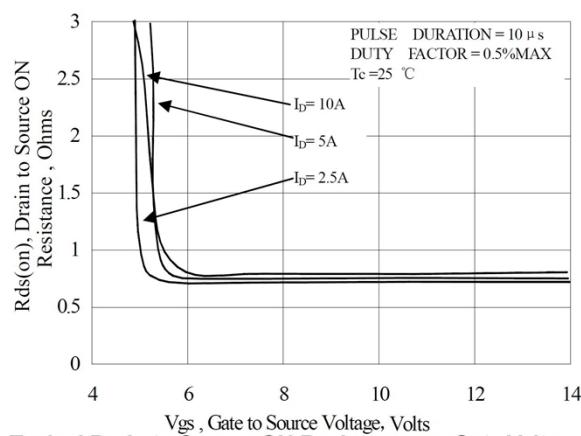


ZL MOSFET

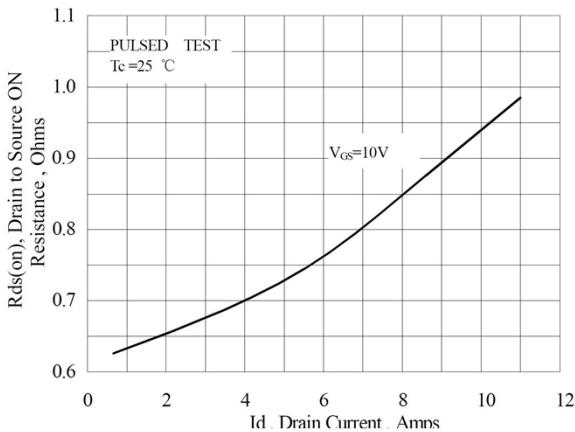
ZL12N70



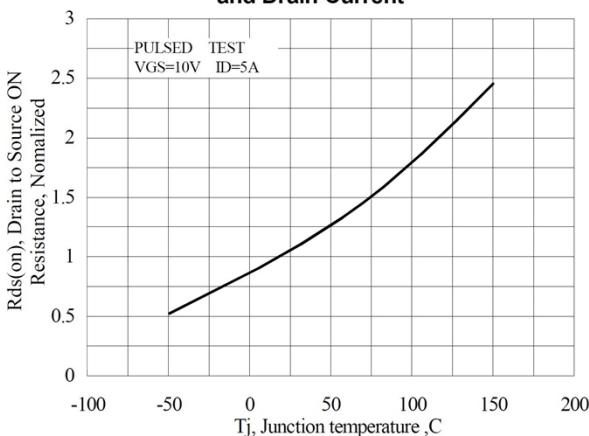
Typical Transfer Characteristics



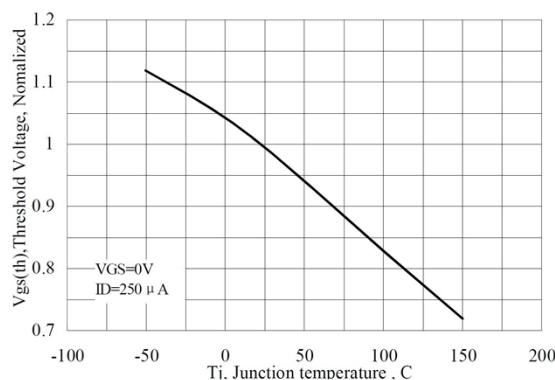
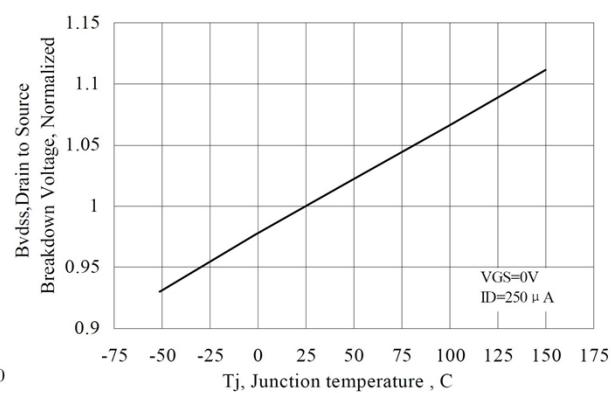
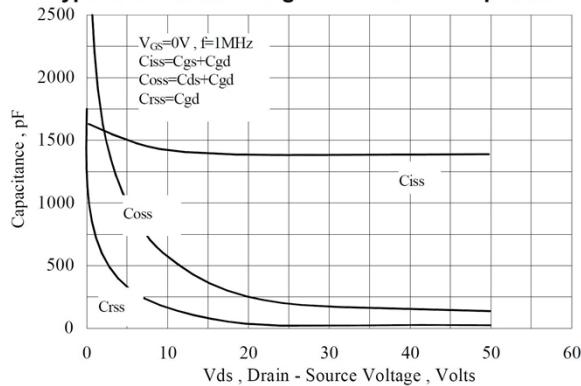
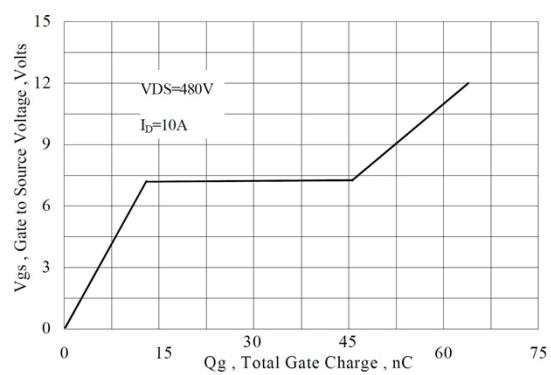
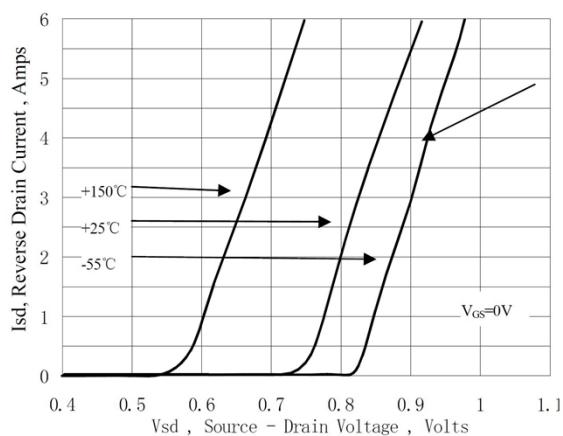
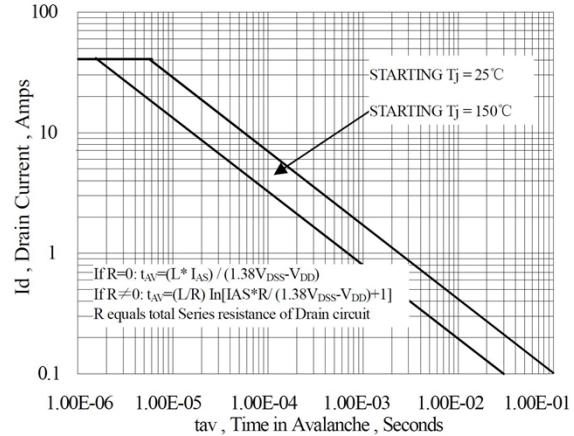
Typical Drain to Source ON Resistance vs Gate Voltage and Drain Current



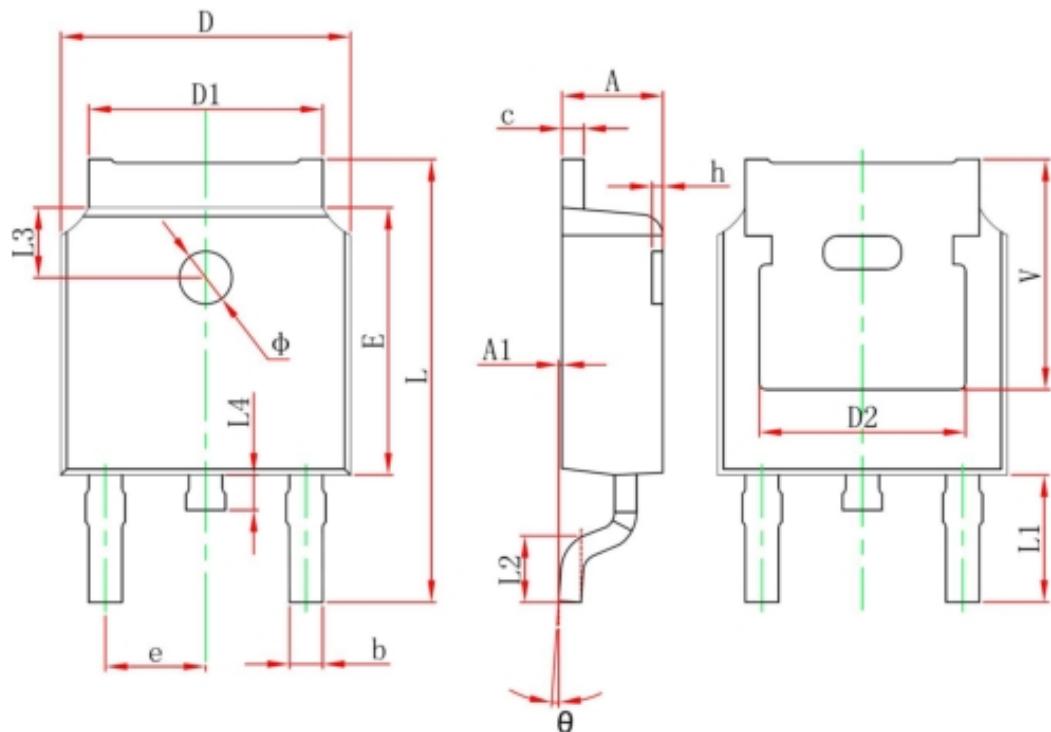
Typical Drain to Source ON Resistance vs Drain Current



Typical Drian to Source on Resistance vs Junction Temperature


Typical Threshold Voltage vs Junction Temperature

Typical Breakdown Voltage vs Junction Temperature

Typical Capacitance vs Drain to Source Voltage

Typical Gate Charge vs Gate to Source Voltage

Typical Body Diode Transfer Characteristics

Maximum Forward Bias Safe Operating Area

TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	